## Sadhvikas Addamane

List of Publications by Year in descending order

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933447 752698 32 420 10 20 citations g-index h-index papers 32 32 32 593 docs citations times ranked citing authors all docs

| #  | Article  | IF  | CITATIONS |
|----|--|-----|-----------|
| 1  | Light-Emitting Metasurfaces: Simultaneous Control of Spontaneous Emission and Far-Field Radiation. Nano Letters, 2018, 18, 6906-6914.  | 9.1 | 126       |
| 2  | Interplay between total thickness and period thickness in the phonon thermal conductivity of superlattices from the nanoscale to the microscale: Coherent versus incoherent phonon transport. Physical Review B, 2018, 97, . | 3.2 | 48        |
| 3  | Perfectly absorbing dielectric metasurfaces for photodetection. APL Photonics, 2020, 5, .  | 5.7 | 33        |
| 4  | Modeling and experimental realization of modelocked VECSEL producing high power sub-100 fs pulses. Applied Physics Letters, 2018, 113, .   | 3.3 | 23        |
| 5  | Terahertz Pulse Generation from GaAs Metasurfaces. ACS Photonics, 2022, 9, 1136-1142.  | 6.6 | 20        |
| 6  | Perfect absorption in GaAs metasurfaces near the bandgap edge. Optics Express, 2020, 28, 35284.  | 3.4 | 15        |
| 7  | InP-Based Waveguide-Integrated Photodiodes With InGaAs/GaAsSb Type-II Quantum Wells and 10-GHz<br>Bandwidth at 2 \$ mathbf {mu }\$m Wavelength. Journal of Lightwave Technology, 2018, 36, 4981-4987.                        | 4.6 | 14        |
| 8  | Multi-Angle VECSEL Cavities for Dispersion Control and Peak-Power Scaling. IEEE Photonics Technology Letters, 2017, 29, 326-329.   | 2.5 | 13        |
| 9  | Epitaxial Regrowth and Hole Shape Engineering for Photonic Crystal Surface Emitting Lasers (PCSELs). Journal of Crystal Growth, 2020, 535, 125531.   | 1.5 | 12        |
| 10 | Highly efficient terahertz photoconductive metasurface detectors operating at microwatt-level gate powers. Optics Letters, 2021, 46, 3159.   | 3.3 | 12        |
| 11 | High-Speed InP-Based p-i-n Photodiodes With InGaAs/GaAsSb Type-II Quantum Wells. IEEE Photonics<br>Technology Letters, 2018, 30, 399-402.  | 2.5 | 11        |
| 12 | InAs FinFETs Performance Enhancement by Superacid Surface Treatment. IEEE Transactions on Electron Devices, 2019, 66, 1856-1861.   | 3.0 | 10        |
| 13 | Thin THz QCL active regions for improved continuous-wave operating temperature. AIP Advances, 2021, $11,\ldots$  | 1.3 | 10        |
| 14 | A Tunable Unidirectional Source for GUSTO's Local Oscillator at 4.74 THz. IEEE Transactions on Terahertz Science and Technology, 2022, 12, 144-150.  | 3.1 | 8         |
| 15 | Active Mediation of Plasmon Enhanced Localized Exciton Generation, Carrier Diffusion and Enhanced Photon Emission. Scientific Reports, 2017, 7, 864.   | 3.3 | 7         |
| 16 | Tunable quantum-cascade VECSEL operating at 1.9 THz. Optics Express, 2021, 29, 34695.  | 3.4 | 7         |
| 17 | Manipulation of quantum dot emission with semiconductor metasurfaces exhibiting magnetic quadrupole resonances. Optics Express, 2021, 29, 5567.  | 3.4 | 6         |
| 18 | Controllable finite ultra-narrow quality-factor peak in a perturbed Dirac-cone band structure of a photonic-crystal slab. Applied Physics Letters, 2021, 119, .  | 3.3 | 6         |

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|----|--|-----|-----------|
| 19 | THz time-domain characterization of amplifying quantum-cascade metasurface. Applied Physics Letters, 2021, 119, .  | 3.3 | 6         |
| 20 | Experimental Evidence of Suppression of Subterahertz Phonons and Thermal Conductivity in GaAs/AlAs Superlattices Due to Extrinsic Scattering Processes. Journal of Physical Chemistry C, 2018, 122, 29577-29585. | 3.1 | 5         |
| 21 | Growth and Optimization of 2-1-1/4m InGaSb/AlGaSb Quantum-Well-Based VECSELs on GaAs/AlGaAs DBRs. IEEE Journal of Selected Topics in Quantum Electronics, 2013, 19, 1700611-1700611.                             | 2.9 | 4         |
| 22 | Isolating GaSb Membranes Grown Metamorphically on GaAs Substrates Using Highly Selective Substrate Removal Etch Processes. Journal of Electronic Materials, 2015, 44, 1327-1331.                                 | 2.2 | 4         |
| 23 | Revealing Temperature-Dependent Absorption and Emission Enhancement Factors in Plasmon Coupled Semiconductor Heterostructures. ACS Applied Electronic Materials, 2019, 1, 1439-1448.                             | 4.3 | 4         |
| 24 | Pixelated GaSb solar cells on silicon by membrane bonding. Applied Physics Letters, 2018, 113, 123502.   | 3.3 | 3         |
| 25 | InGaSb Defect Filter Layer to Improve Performance of GaSb Solar Cells Grown on GaAs Substrates.<br>Journal of Electronic Materials, 2020, 49, 7153-7158.   | 2.2 | 3         |
| 26 | Multi-mode lasing in terahertz metasurface quantum-cascade VECSELs. Applied Physics Letters, 2021, 119, 111103.  | 3.3 | 3         |
| 27 | Optically Pumped 1 $\hat{l}\frac{1}{4}$ m Low Threshold Photonic Crystal Surface Emitting Lasers Grown on GaAs Substrate. , 2019, , .  |     | 2         |
| 28 | A transmission electron microscopy study of dislocation propagation and filtering in highly mismatched GaSb/GaAs heteroepitaxy. Journal of Applied Physics, 2020, 128, 225301.                                   | 2.5 | 2         |
| 29 | Submonolayer Quantum-Dot Based Saturable Absorber for Femtosecond Pulse Generation. Journal of Electronic Materials, 2021, 50, 2710-2715.  | 2.2 | 2         |
| 30 | Investigation of Surface Defects in AlInSb Metamorphic Buffer (MB) Grown on GaSb. Journal of Electronic Materials, 2016, 45, 6258-6264.  | 2.2 | 1         |
| 31 | Molecular beam epitaxy of high-resistivity AISb for room-temperature radiation detectors. , 2015, , .  |     | 0         |
| 32 | High-speed type-II InGaAs/GaAsSb multiple quantum-well integrated waveguide photodiodes at 2 $\hat{l}$ 4m wavelength. , 2017, , .  |     | 0         |